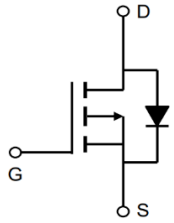
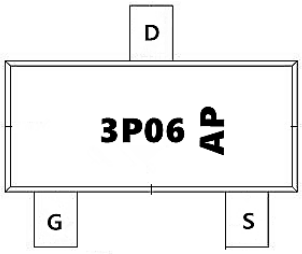
AP3P06BI

-60V P-Channel Enhancement Mode MOSFET

Description

The AP3P06BI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.





General Features

V_{DS} = -60V I_D =-2.8A

$R_{DS(ON)}$ < 200mΩ @ V_{GS}=-10V （**Type：165mΩ**）

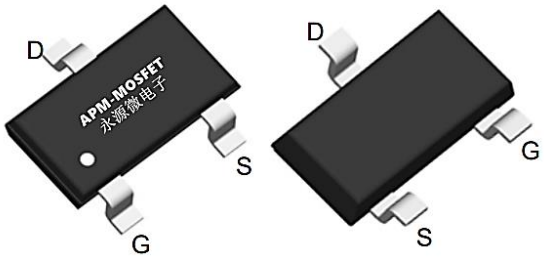
Application

Battery protection

Load switch

Uninterruptible power supply

Top View **Bottom View**



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP3P06BI	SOT23L	3P06- AP	3000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-2.8	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ -10V[1]	-1.8	A
I_{DM}	Pulsed Drain Current[2]	-8.4	A
P_D@T_A=25℃	Total Power Dissipation[3]	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	125	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	80	℃/W

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Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	-67	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.021	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-1.5A	---	165	200	mΩ
		V_{GS}=-4.5V , I_D=-1A	---	200	250	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	1.7	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.08	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-48V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-1.5A	---	5.9	---	S
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-20V , V_{GS}=-4.5V , I_D=-1.5A	---	4.6	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	1.62	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=-15V , V_{GS}=-10V , R_G=3.3Ω, I_D=-1A	---	17.4	---	ns
T_r	Rise Time		---	5.4	---	
$T_{d(off)}$	Turn-Off Delay Time		---	37.2	---	
T_f	Fall Time		---	2.4	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	453	---	pF
C_{oss}	Output Capacitance		---	59	---	
C_{rss}	Reverse Transfer Capacitance		---	38	---	
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	-1.7	A
I_{SM}	Pulsed Source Current[2,4]		---	---	-7	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :

1、The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The power dissipation is limited by 150℃ junction temperature

4、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

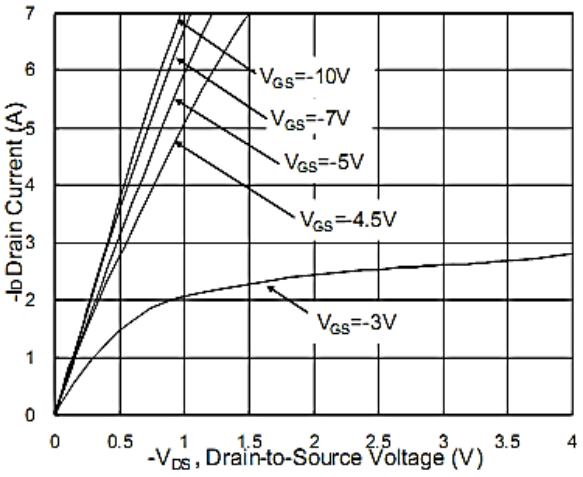

Fig.1 Typical Output Characteristics

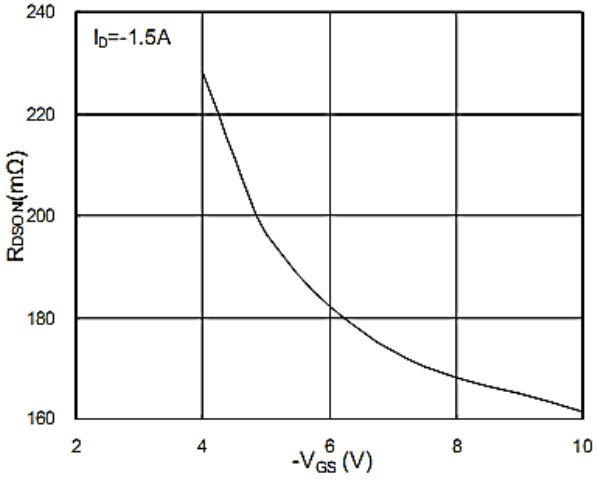

Fig.2 On-Resistance v.s Gate-Source

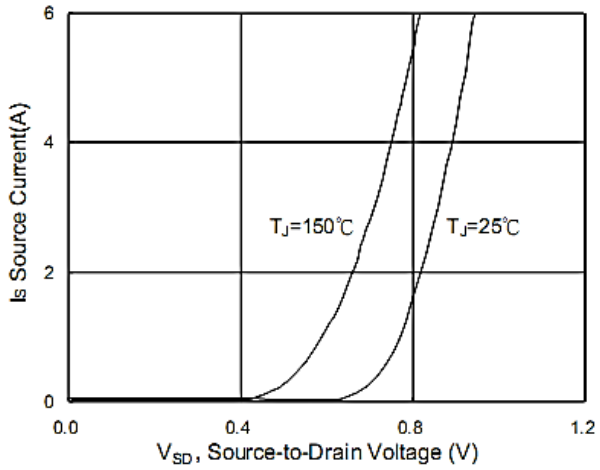

Fig.3 Forward Characteristics Of Reverse

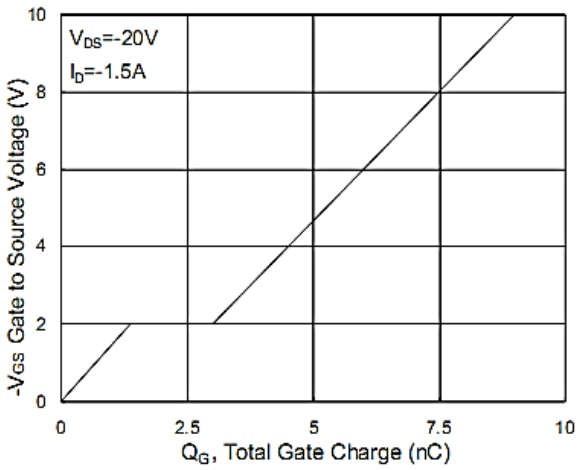

Fig.4 Gate-Charge Characteristics

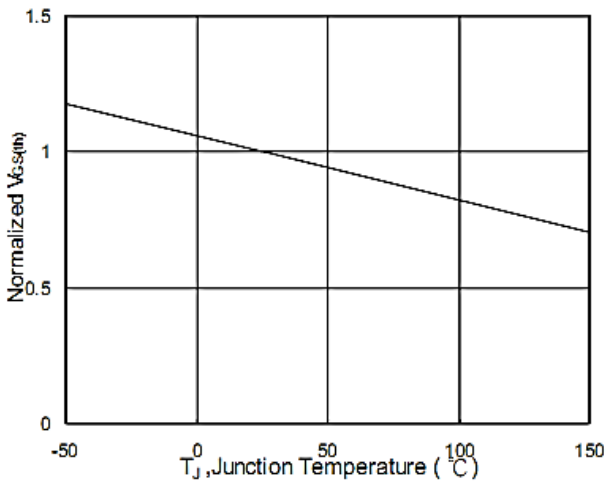

Fig.5 Normalized $V_{GS(th)}$ v.s T_J

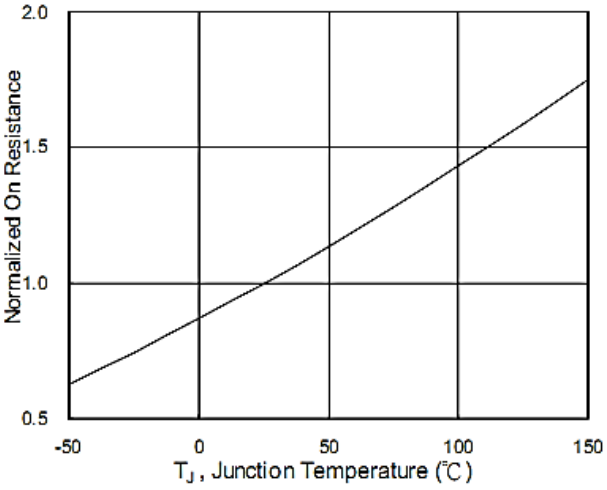

Fig.6 Normalized R_{DSON} v.s T_J

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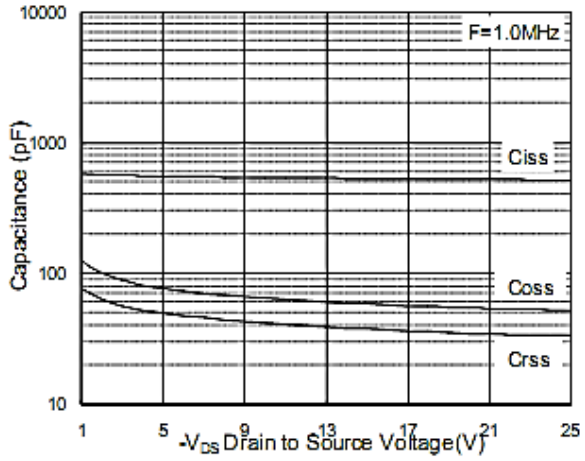


Fig.7 Capacitance

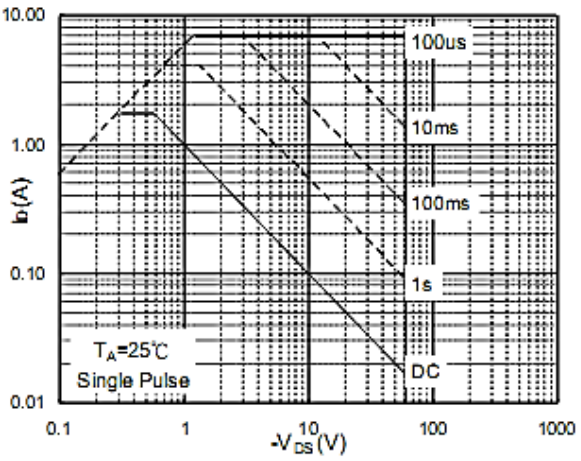


Fig.8 Safe Operating Area

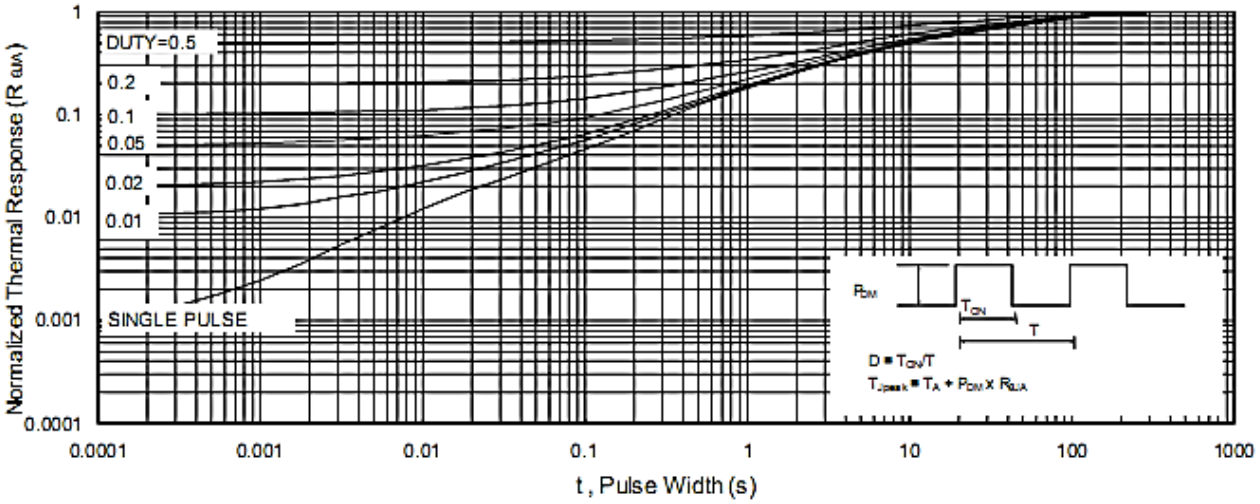


Fig.9 Normalized Maximum Transient Thermal Impedance

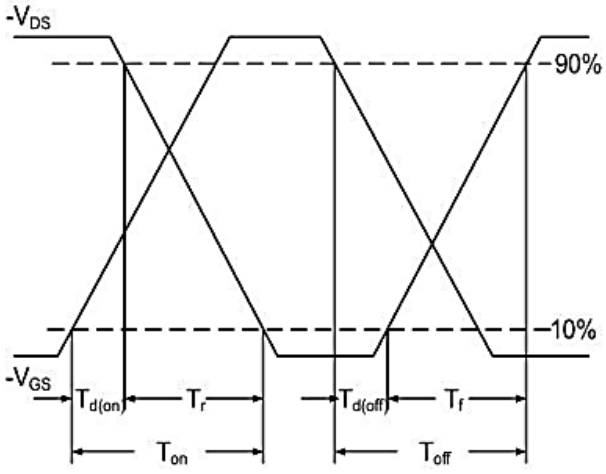


Fig.10 Switching Time Waveform

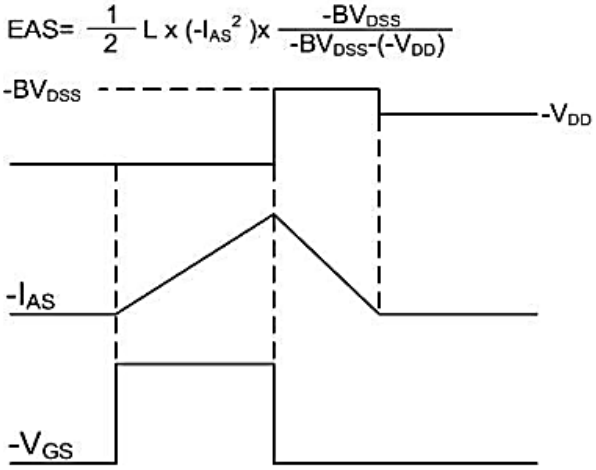
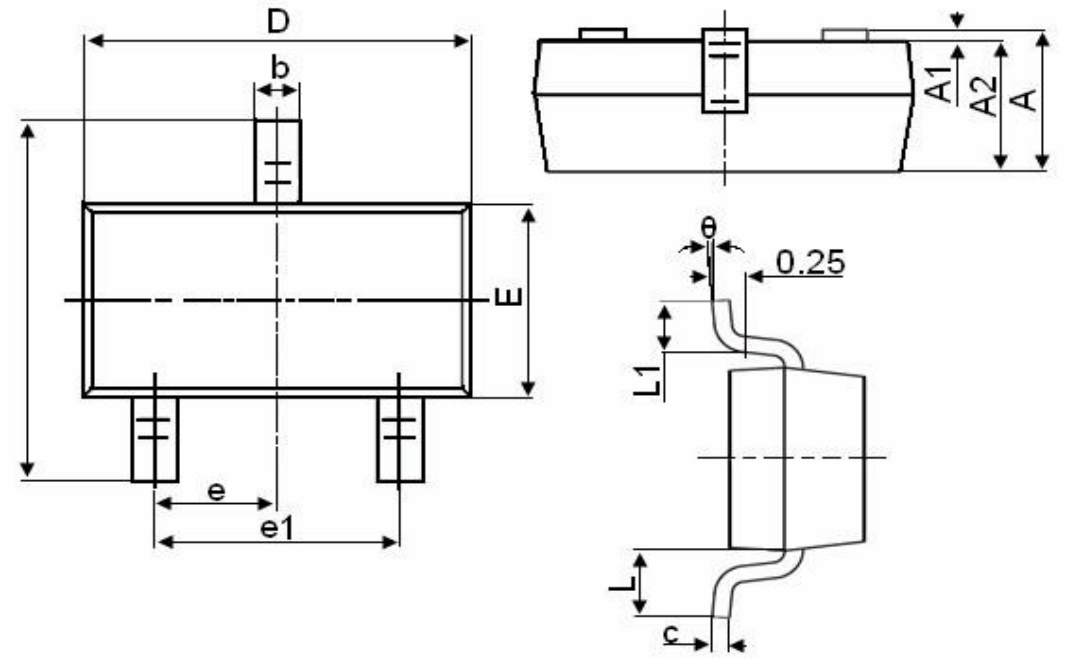


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data-SOT23-XC-Single



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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Edition	Date	Change
RVE1.0	2021/3/1	Initial release